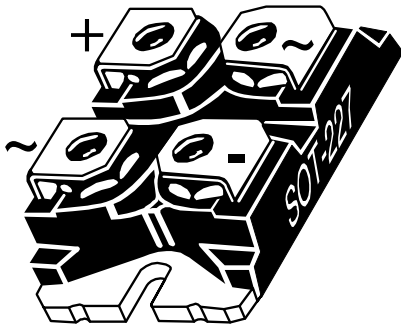
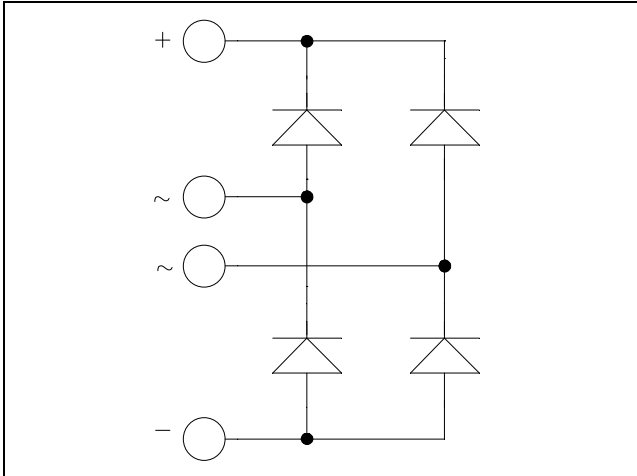


ISOTOP[®] Fast Diode Full Bridge Power Module

$V_{RRM} = 1200V$
 $I_C = 30A @ T_c = 80^{\circ}C$



Application

- Switch mode power supplies rectifier
- Induction heating
- Welding equipment
- High speed rectifiers

Features

- Ultra fast recovery times
- Soft recovery characteristics
- High blocking voltage
- High current
- Low leakage current
- Very low stray inductance
- High level of integration
- ISOTOP[®] Package (SOT-227)

Benefits

- Outstanding performance at high frequency operation
- Low losses
- Low noise switching
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit	
V_R	Maximum DC reverse Voltage	1200	V	
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			
$I_{F(AV)}$	Maximum Average Forward Current	Duty cycle = 50%	$T_C = 25^{\circ}C$	A
			$T_C = 80^{\circ}C$	
I_{FSM}	Non-Repetitive Forward Surge Current	8.3ms	$T_J = 45^{\circ}C$	210

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_F	Diode Forward Voltage	$I_F = 30\text{A}$		2.5	3.1	V
		$I_F = 60\text{A}$		3.2		
		$I_F = 30\text{A}$	$T_j = 125^\circ\text{C}$		1.8	
I_{RM}	Maximum Reverse Leakage Current	$V_R = 1200\text{V}$	$T_j = 25^\circ\text{C}$		100	μA
			$T_j = 125^\circ\text{C}$		500	
C_T	Junction Capacitance	$V_R = 200\text{V}$		28		pF

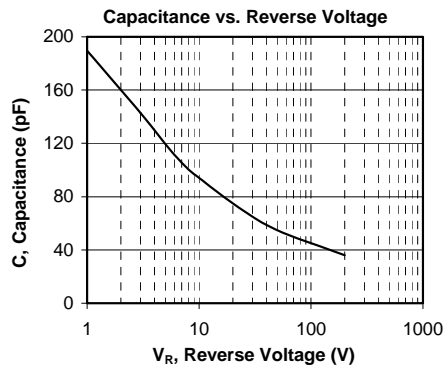
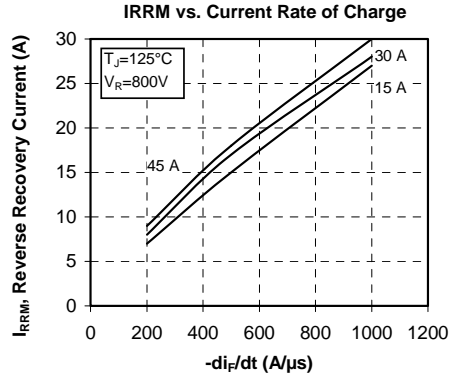
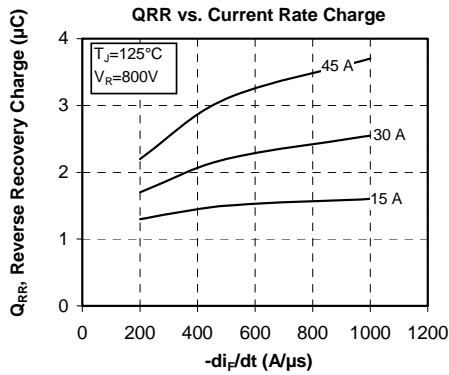
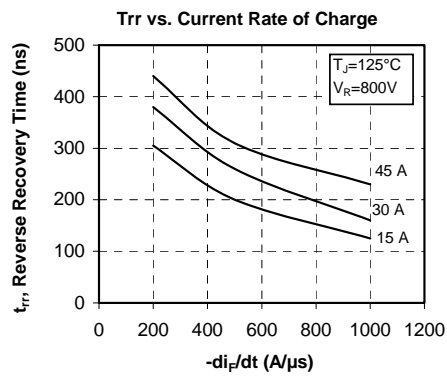
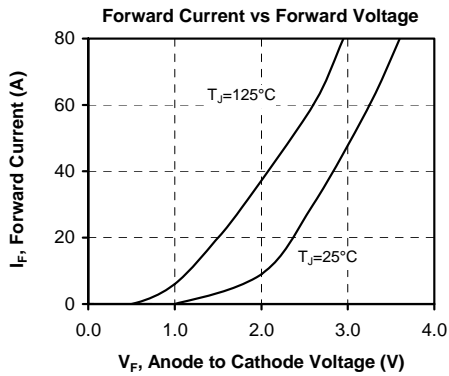
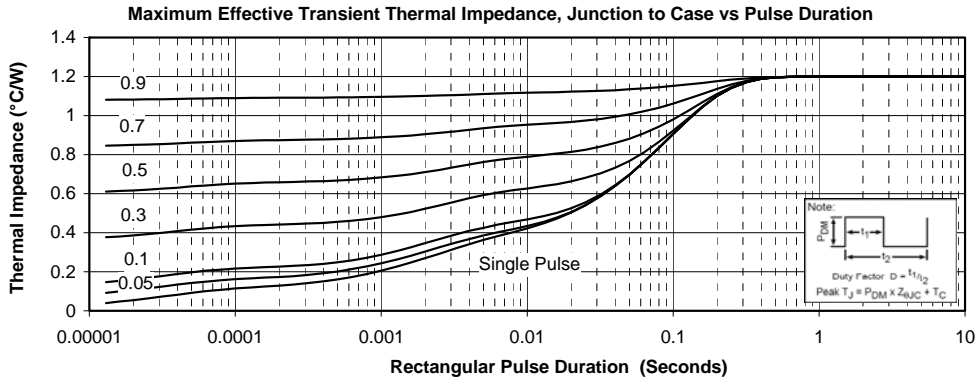
Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
t_{rr}	Reverse Recovery Time	$I_F = 30\text{A}$ $V_R = 800\text{V}$ $di/dt = 200\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		300	ns
			$T_j = 125^\circ\text{C}$		380	
Q_{rr}	Reverse Recovery Charge	$I_F = 30\text{A}$ $V_R = 800\text{V}$ $di/dt = 200\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		360	nC
			$T_j = 125^\circ\text{C}$		1700	
I_{RRM}	Reverse Recovery Current	$I_F = 30\text{A}$ $V_R = 800\text{V}$ $di/dt = 200\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		4	A
			$T_j = 125^\circ\text{C}$		8	
t_{rr}	Reverse Recovery Time	$I_F = 30\text{A}$ $V_R = 800\text{V}$ $di/dt = 1000\text{A}/\mu\text{s}$	$T_j = 125^\circ\text{C}$		160	ns
Q_{rr}	Reverse Recovery Charge				2550	nC
I_{RRM}	Reverse Recovery Current				28	A

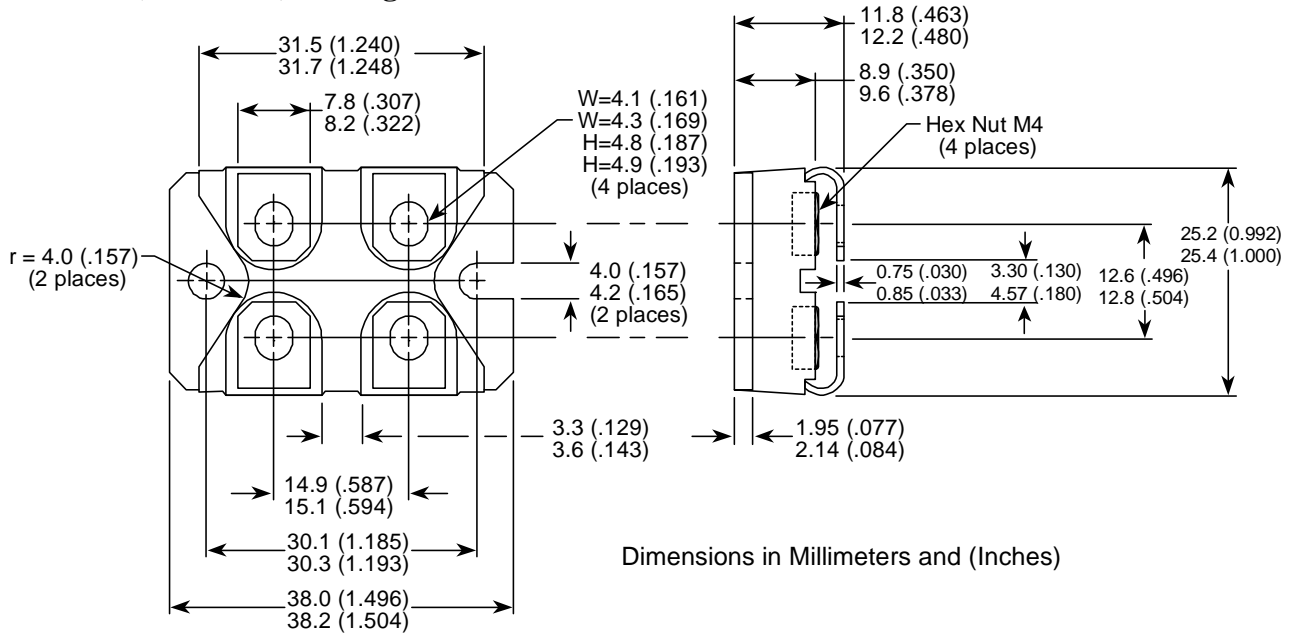
Thermal and package characteristics

Symbol	Characteristic	Min	Typ	Max	Unit
R_{thJC}	Junction to Case Thermal resistance			1.2	$^\circ\text{C}/\text{W}$
R_{thJA}	Junction to Ambient			20	
V_{ISOL}	RMS Isolation Voltage, any terminal to case $t = 1\text{ min}$, $I_{isol} < 1\text{mA}$, 50/60Hz	2500			V
T_J, T_{STG}	Storage Temperature Range	-55		175	$^\circ\text{C}$
T_L	Max Lead Temp for Soldering: 0.063" from case for 10 sec			300	
Torque	Mounting torque (Mounting = 8-32 or 4mm Machine and terminals = 4mm Machine)			1.5	N.m
Wt	Package Weight		29.2		g

Typical Performance Curve



SOT-227 (ISOTOP®) Package Outline



ISOTOP® is a registered trademark of ST Microelectronics NV

Microsemi reserves the right to change, without notice, the specifications and information contained herein

Microsemi's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 6,939,743 7,352,045 5,283,201 5,801,417 5,648,283 7,196,634 6,664,594 7,157,886 6,939,743 7,342,262 and foreign patents. U.S. and Foreign patents pending. All Rights Reserved.